Plastic NPN Silicon High-Voltage Power Transistor

... designed for use in line-operated equipment such as audio output amplifiers; low-current, high-voltage converters; and AC line relays.

- Excellent DC Current Gain hFE = 30-250 @ IC = 100 mAdc
- Current–Gain Bandwidth Product
 - fT = 10 MHz (Min) @ IC = 50 mAdc

MAXIMUM RATINGS (1)

Rating	Symbol	2N5655	2N5656	2N5657	Unit
Collector–Emitter Voltage	VCEO	250	300	350	Vdc
Collector–Base Voltage	V _{CB}	275	325	375	Vdc
Emitter-Base Voltage	V _{EB}	6.0			Vdc
Collector Current — Continuous Peak	IC	0.5 1.0			Adc
Base Current	۱ _B	0.25			Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	20 0.16			Watts W/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	-65 to +150			°C



0.5 AMPERE POWER TRANSISTORS NPN SILICON 250-300-350 VOLTS 20 WATTS



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	6.25	°C/W

(1) Indicates JEDEC Registered Data.



Figure 1. Power Derating





Safe Area Limits are indicated by Figures 3 and 4. Both limits are applicable and must be observed.



2N5655 2N5656 2N5657

*ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				-	-
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc (inductive), L = 50 mH)	2N5655 2N5656 2N5657	VCEO(sus)	250 300 350		Vdc
Collector–Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5655 2N5656 2N5657	V(BR)CEO	250 300 350	_ _ _	Vdc
Collector Cutoff Current $(V_{CE} = 150 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 200 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 250 \text{ Vdc}, I_B = 0)$	2N5655 2N5656 2N5657	ICEO		0.1 0.1 0.1	mAdc
Collector Cutoff Current ($V_{CE} = 250 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 300 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 350 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 150 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$) ($V_{CE} = 250 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$) ($V_{CE} = 250 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$)	2N5655 2N5656 2N5657 2N5655 2N5655 2N5656 2N5657	ICEX	 	0.1 0.1 1.0 1.0 1.0	mAdc
Collector Cutoff Current $(V_{CB} = 275 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 325 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 375 \text{ Vdc}, I_E = 0)$	2N5655 2N5656 2N5657	ICBO	 	10 10 10	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_{C} = 0$)		IEBO		10	μAdc
ON CHARACTERISTICS					
DC Current Gain (1) ($I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 250 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)		hFE	25 30 15 5.0	 250 	_
Collector–Emitter Saturation Voltage (1) ($I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc}$) ($I_C = 250 \text{ mAdc}, I_B = 25 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 100 \text{ mAdc}$)		VCE(sat)		1.0 2.5 10	Vdc
Base–Emitter Voltage (1) $(I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$		VBE	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (2) $(I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 10 \text{ MHz})$		fT	10	-	MHz
Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f = 100 kHz)		Cob		25	pF
Small–Signal Current Gain (I_C = 100 mAdc, V_{CE} = 10 Vdc, f = 1.0 k	Small–Signal Current Gain (I _C = 100 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		20	—	—

* Indicates JEDEC Registered Data for 2N5655 Series.

(1) Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



Figure 3. Active–Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

2N5655 2N5656 2N5657







Figure 5. "On" Voltages



Figure 6. Capacitance



Figure 8. Turn–Off Time



Figure 7. Turn-On Time

PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and (\widehat{M}) are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447 JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

